

IN THE CLAIMS:

Please cancel claims 11-21 and 24-27. **Please also amend** claims 22 and 23 as shown in the complete list of claims that is presented below.

1. (previously presented) An ESD protection apparatus for dual-polarity input pad, comprising:

a first region of a first conductivity type;

a second region of a second conductivity type opposite to said first conductivity type formed in said first region;

a third region of said first conductivity type formed in said second region;

a first input connection region of said first conductivity type and a second input connection region of said second conductivity type both formed in said third region; and

a first ground connection region of said first conductivity type and a second ground connection region of said second conductivity type both formed in said first region, at locations that do not overlap the second region or the third region.

2. (original) An ESD protection apparatus of claim 1, further comprising a bridge region of said second conductivity type across said second region and extending to said first and third regions.

3. (previously presented) An ESD protection apparatus of claim 1, wherein said first region is provided by a semiconductor substrate.

4. (original) An ESD protection apparatus of claim 1, wherein said first, second, and third regions are arranged in a triple-well manner.

5. (previously presented) An ESD protection apparatus of claim 1, wherein said first and second input connection regions are connected to an input pad, and said first and second ground connection regions are connected to a ground pad.

6. (original) An ESD protection apparatus of claim 1, wherein said first input connection region, third region, second region, first region, and first and second ground connection regions form an SCR circuit under a positive polarity ESD event.

7. (original) An ESD protection apparatus of claim 1, wherein said first and second input connection regions, third region, second region, first region, and first ground connection region form an SCR circuit under a negative polarity ESD event.

8. (original) An ESD protection apparatus of claim 1, wherein said first, second and third regions form two back-to-back diodes under a normal operation.

9. (original) An ESD protection apparatus of claim 2, wherein said bridge region breaks down to said first region under a positive polarity ESD event.

10. (original) An ESD protection apparatus of claim 2, wherein said bridge region breaks down to said third region under a negative polarity ESD event.

Claims 11-21 (cancelled).

22. (currently amended) An ESD protection ~~method~~ apparatus of claim 6, 19, ~~further comprising forcing wherein breakdown of a junction breakdown at between~~ said second ~~semiconductor region~~ and third regions is forced under a positive polarity ESD event.

23. (currently amended) An ESD protection ~~method~~ apparatus of claim 7, 19, ~~further comprising forcing wherein breakdown of a junction breakdown at between~~ said first ~~semiconductor region~~ and second regions is forced under a negative polarity ESD event.

Claims 24-27 (cancelled).